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2STC4468

High power NPN epitaxial planar bipolar transistor

Features

- High breakdown voltage $V_{CE0} = 140\text{ V}$
- Complementary to 2STA1695
- Typical $f_t = 20\text{ MHz}$
- Fully characterized at $125\text{ }^\circ\text{C}$

Application

- Audio power amplifier

Description

This device is an NPN transistor manufactured using BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor exhibits good gain linearity behavior. Recommended for 70 W to 100 W high fidelity audio frequency amplifier output stages.

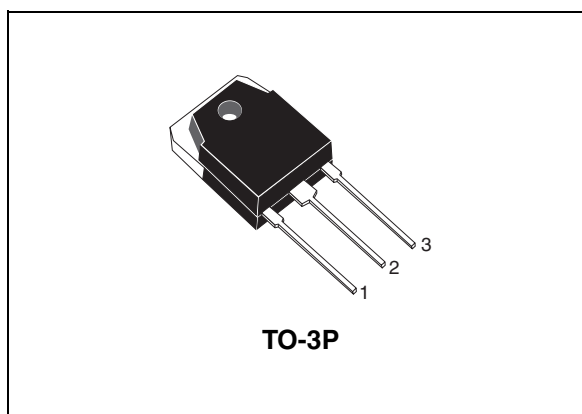


Figure 1. Internal schematic diagram

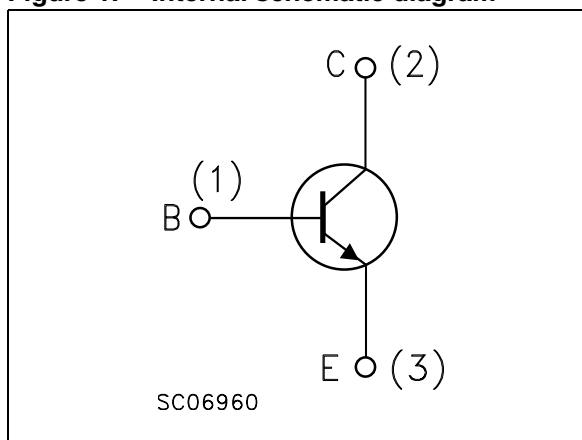


Table 1. Device summary

Order code	Marking	Package	Packaging
2STC4468	2STC4468	TO-3P	Tube

Electrical ratings

2STC4468

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage ($I_E = 0$)	200	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	140	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	6	V
I_C	Collector current	10	A
I_{CM}	Collector peak current ($t_P < 5$ ms)	20	A
P_{tot}	Total dissipation at $T_C = 25$ °C	100	W
T_{stg}	Storage temperature	-65 to 150	°C
T_J	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.25	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max	35.7	°C/W

2 Electrical characteristics

($T_{case} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector cut-off current ($I_E = 0$)	$V_{CB} = 200\text{ V}$			0.1	μA
I_{EBO}	Emitter cut-off current ($I_C = 0$)	$V_{EB} = 6\text{ V}$			0.1	μA
$V_{(BR)CEO}^{(1)}$	Collector-emitter breakdown voltage ($I_B = 0$)	$I_C = 50\text{ mA}$	140			V
$V_{(BR)CBO}$	Collector-base breakdown voltage ($I_E = 0$)	$I_C = 100\text{ }\mu\text{A}$	200			V
$V_{(BR)EBO}^{(1)}$	Emitter-base breakdown voltage ($I_C = 0$)	$I_E = 1\text{ mA}$	6			V
$V_{CE(sat)}^{(1)}$	Collector-emitter saturation voltage	$I_C = 5\text{ A}$ $I_B = 500\text{ mA}$ $I_C = 7\text{ A}$ $I_B = 700\text{ mA}$			0.5 0.7	V V
V_{BE}	Base-emitter voltage	$V_{CE} = 5\text{ V}$ $I_C = 5\text{ A}$			1.3	V
h_{FE}	DC current gain	$I_C = 3\text{ A}$ $V_{CE} = 4\text{ V}$ $I_C = 5\text{ A}$ $V_{CE} = 4\text{ V}$	70 50		140	
f_T	Transition frequency	$I_C = 0.5\text{ A}$ $V_{CE} = 12\text{ V}$		20		MHz
C_{CBO}	Collector-base capacitance ($I_E = 0$)	$V_{CB} = 10\text{ V}$ $f = 1\text{ MHz}$		150		pF
t_{on}	Resistive Load Turn-on time	$V_{CC} = 60\text{ V}$ $I_C = 5\text{ A}$ $I_{B1} = -I_{B2} = 0.5\text{ A}$		0.22		μs
t_{stg}	Storage time			4.3		μs
t_f	Fall time			0.5		μs

1. Pulse duration = 300 μs , duty cycle $\leq 1.5\%$

Electrical characteristics

2STC4468

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

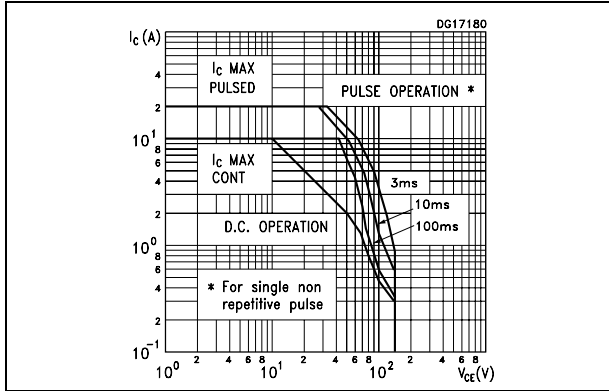


Figure 3. Power derating versus temperature

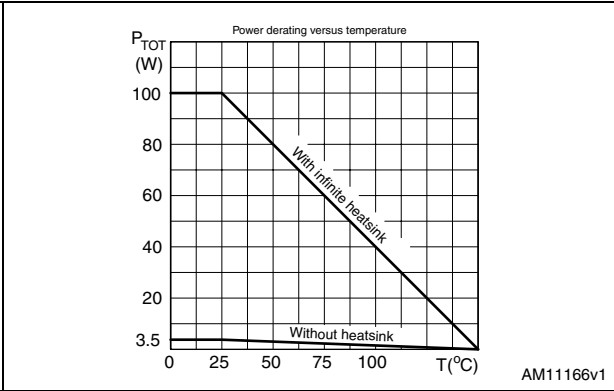


Figure 4. Output characteristics

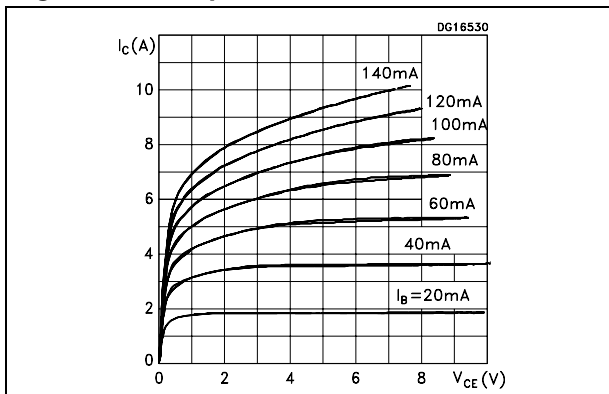


Figure 5. DC current gain

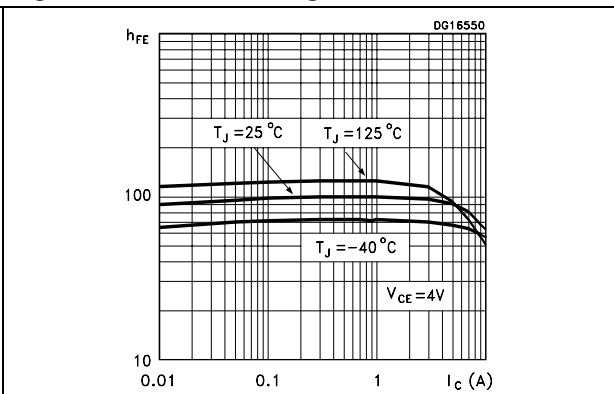
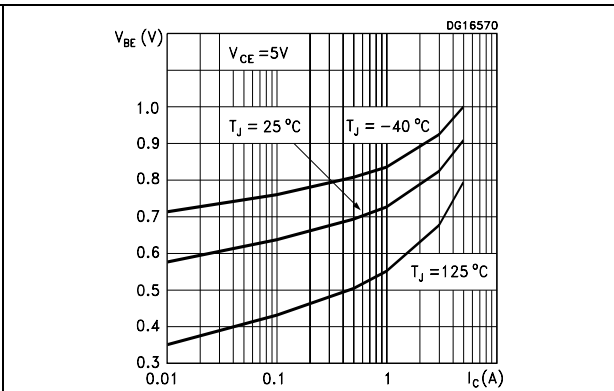
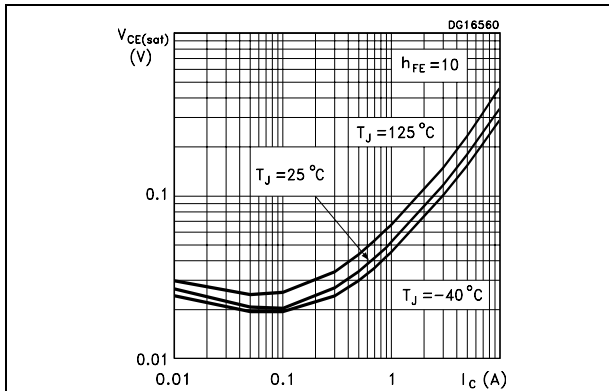


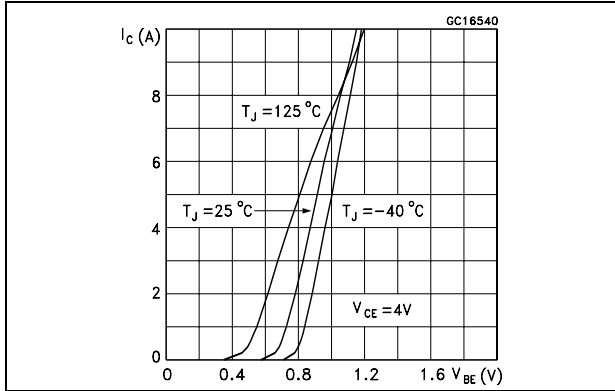
Figure 6. Collector-emitter saturation voltage **Figure 7. Base-emitter voltage**



2STC4468

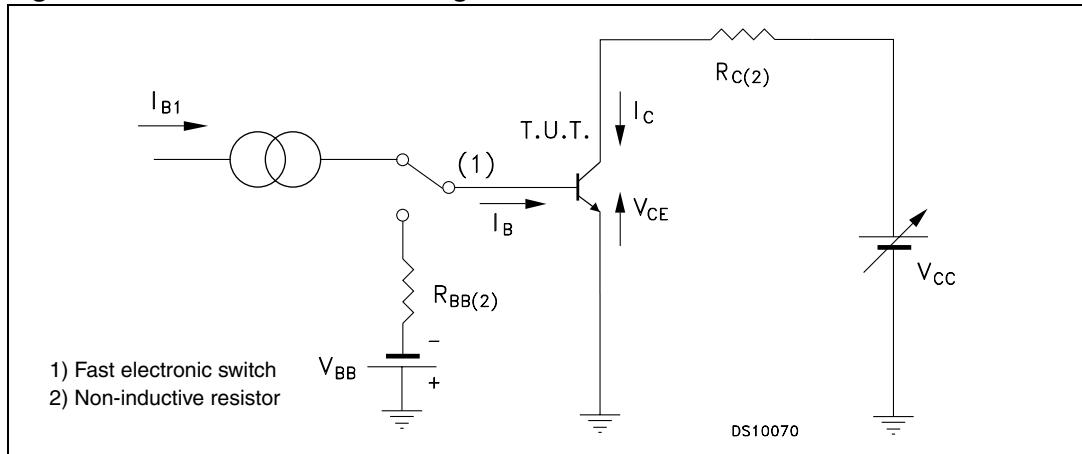
Electrical characteristics

Figure 8. Base-emitter voltage



2.2 Test circuit

Figure 9. Resistive load switching test circuit



3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

2STC4468

Package mechanical data

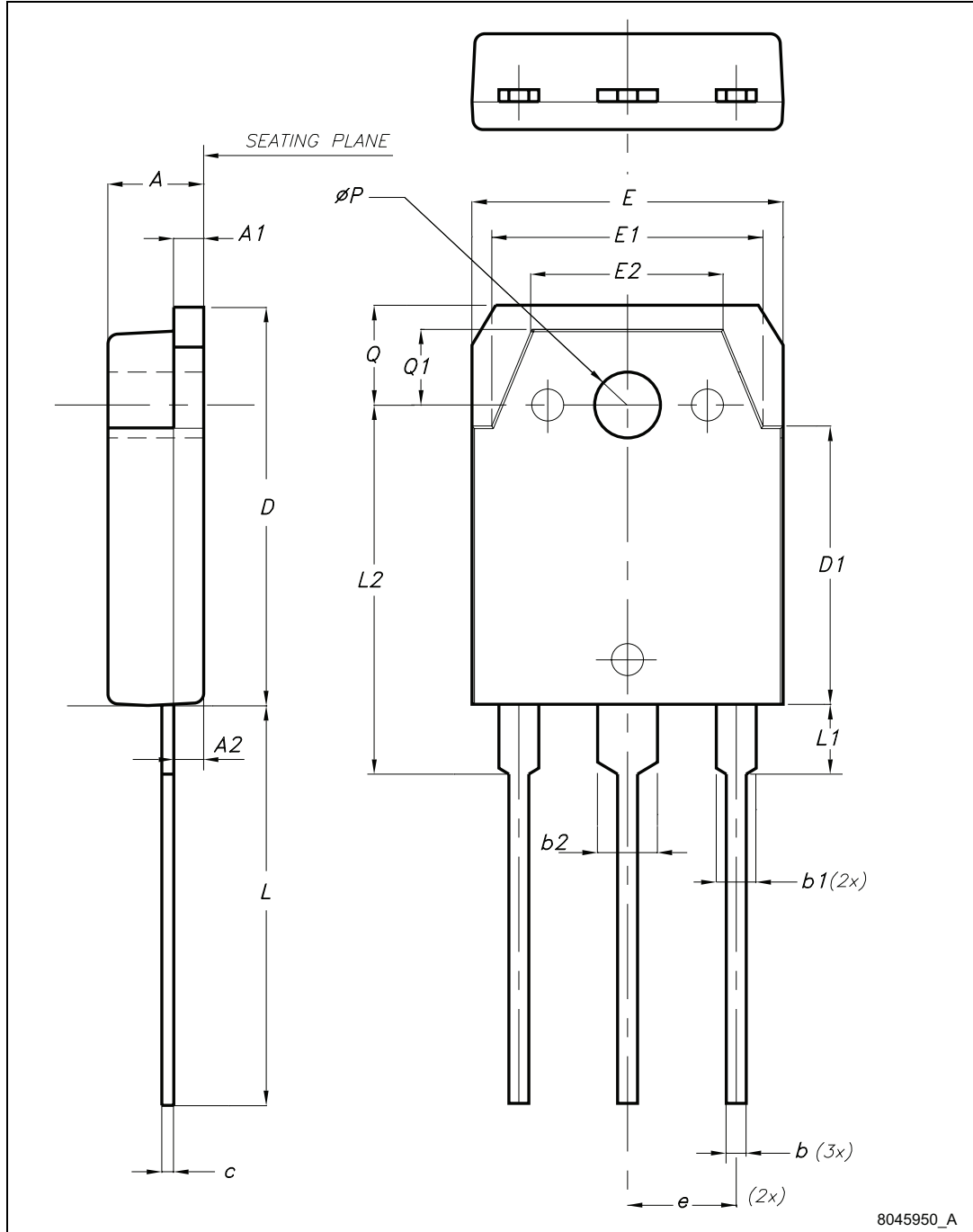
Table 5. TO-3P mechanical data

Dim.	mm		
	Min.	Typ.	Max
A	4.60		5
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1	1.20
b1	1.80		2.20
b2	2.80		3.20
c	0.55	0.60	0.75
D	19.70	19.90	20.10
D1		13.90	
E	15.40		15.80
E1		13.60	
E2		9.60	
e	5.15	5.45	5.75
L	19.50	20	20.50
L1		3.50	
L2	18.20	18.40	18.60
øP	3.10		3.30
Q		5	
Q1		3.80	

Package mechanical data

2STC4468

Figure 10. TO-3P package dimensions



4 Revision history

Table 6. Document revision history

Date	Revision	Changes
21-May-2007	1	Initial release
07-Nov-2008	2	Document status promoted from preliminary data to datasheet.
08-Feb-2012	3	– <i>Figure 3</i> inserted – Mechanical data updated

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